

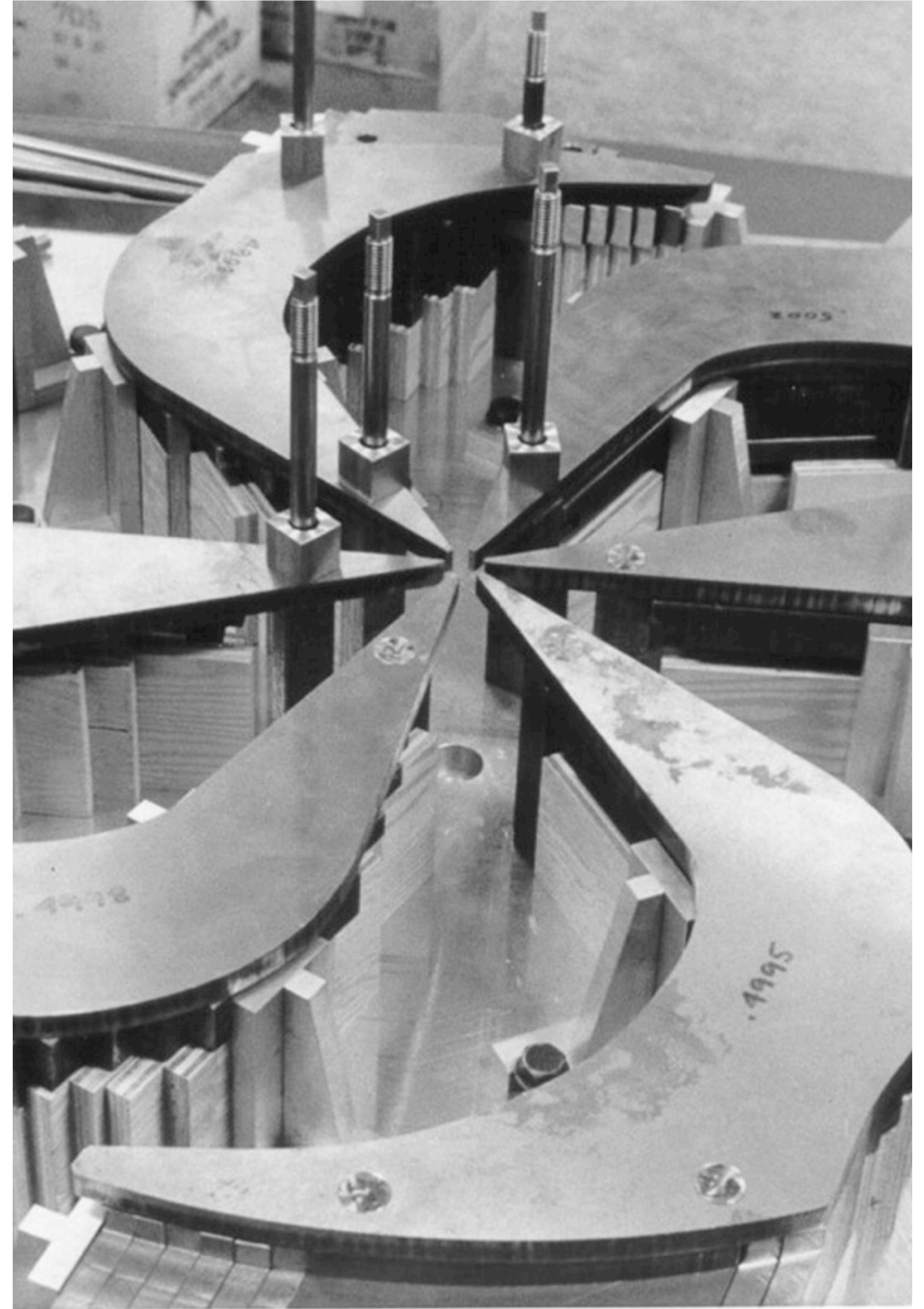
Ultrafast Stimulation of Single Photon Avalanche Diodes with Broad Spectrum Light Source

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TRUST

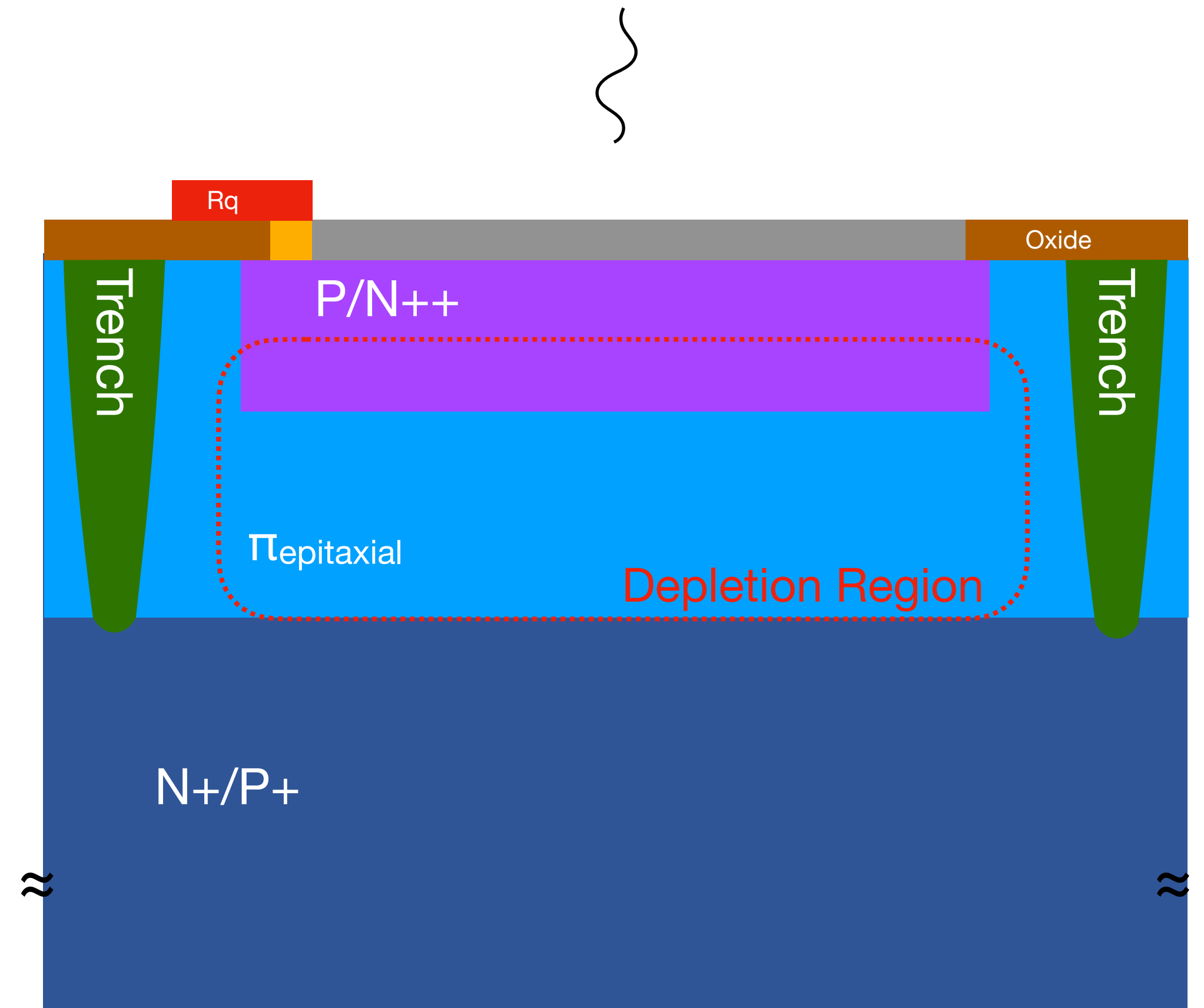


Science Motivation for Fast Timing Characterisation

- **Some of the biggest drivers for the adoption of SPADs include**
 - Fast timing ~10ps resolution
 - Single photon counting
 - High Photon Detection Efficiency (PDE)
- **As the technology matures we see more and more applications aiming to utilise these devices to their full potential.**
 - This requires characterisation and diagnostic techniques that can keep up!
 - Understanding their response allows us to discover new applications.
- **At TRIUMF we have developed an experimental setup for the comprehensive characterisation of SPAD devices**
 - Temperature control (300K - 77K)
 - Optical focus
 - Imaging/Spectroscopy
 - Femtosecond laser
 - Tunable wavelength 310 nm - 2800nm
 - Two-Photon Absorption (maybe)
- **Help drive Research & Development and design through data driven models.**
- **Promote Collaboration.**

Understanding SPAD Response

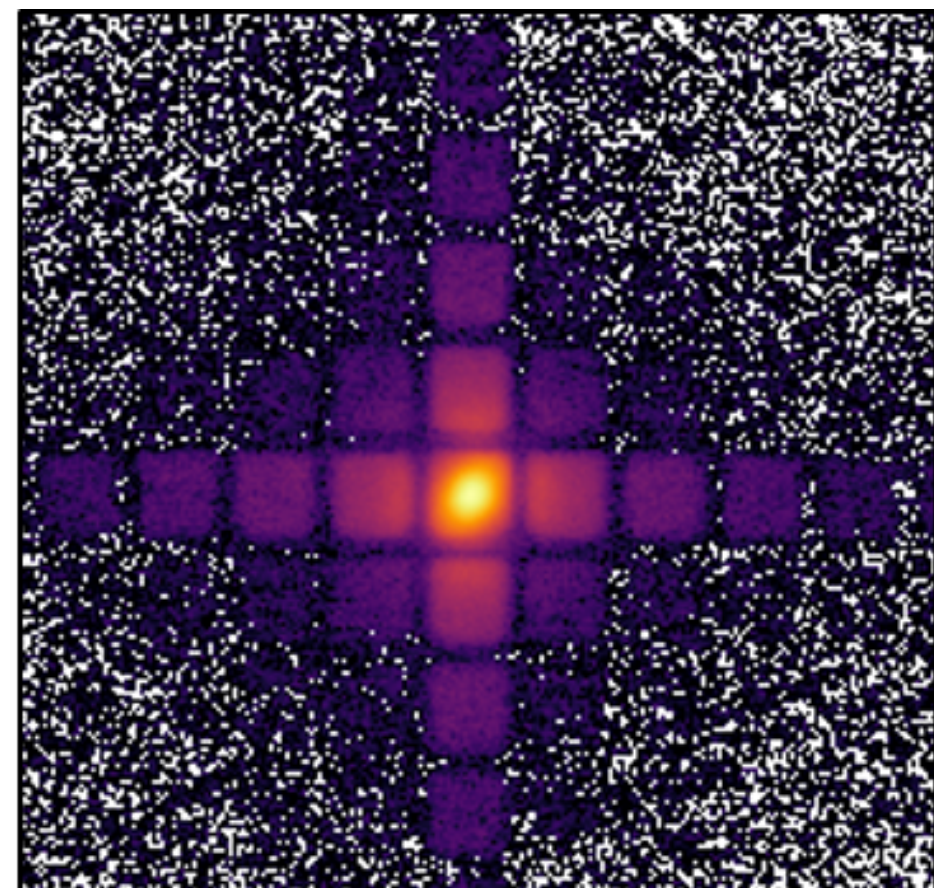
- **Timing resolution**
 - Femtosecond pulse widths allows for the photonics to be factored out of the characterisation
- **sensitivity**
 - Depth deposition depends on wavelength
- **Device noise characteristics?**
 - Optical Cross Talk
 - Trench Effectiveness
 - Secondary emission
- **Temperature Characteristics**
 - Some applications require cryogenic cooling



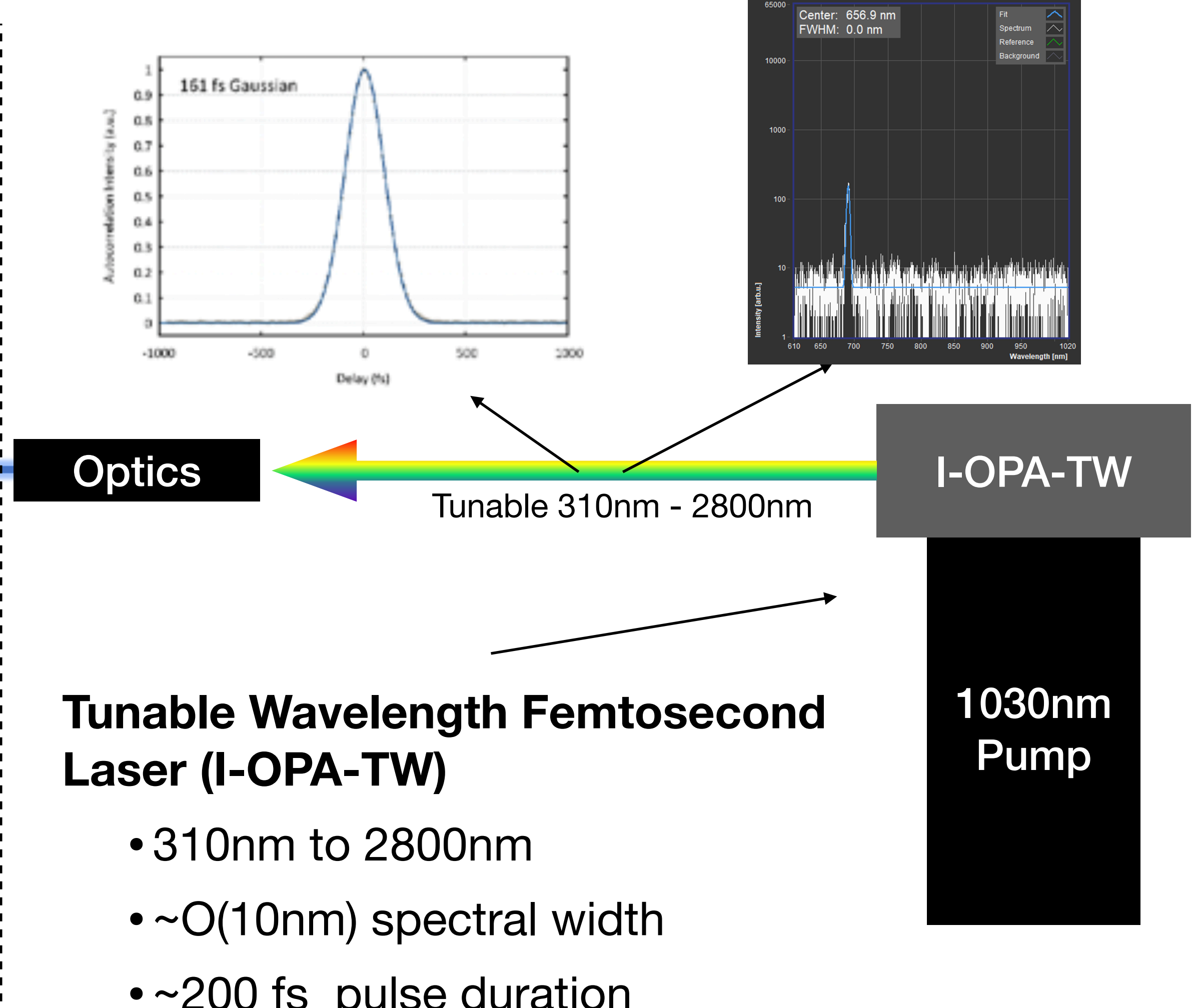
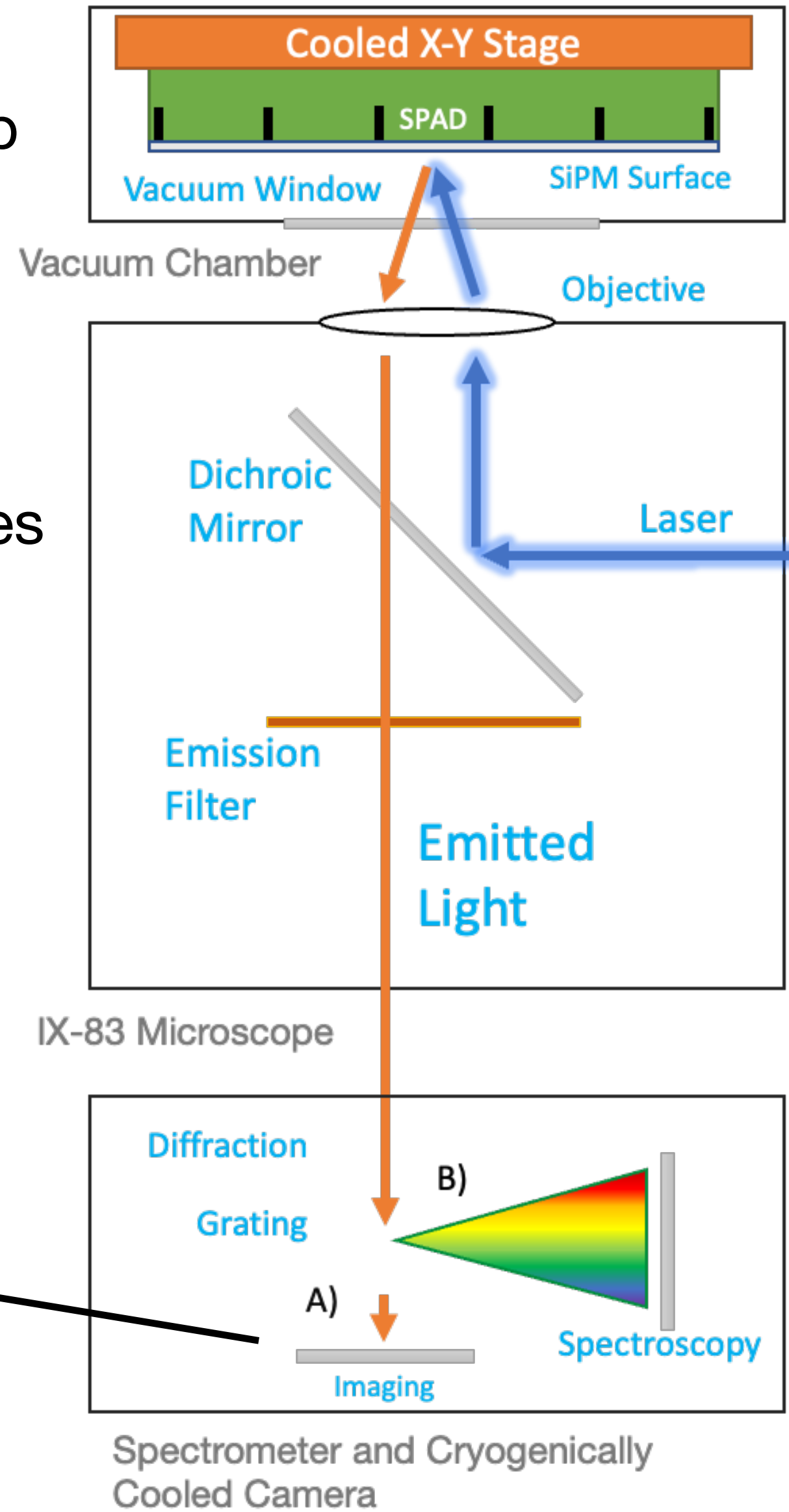
With the Microscope for Injection and Emission of Light (MIEL), we can probe all these features

UltraFast Stimulation with MIEL + I-OPA

- **Temperature control**
 - PDI Controlled LN2 Pump
- **Positional Control**
 - Sub-micron precision
- **Focus control**
 - Interchangeable objectives
- **Imaging/Spectroscopy**
 - LN2 cooled CCD
 - Princeton Instruments Spectrometer



Seraphim Koulosouas



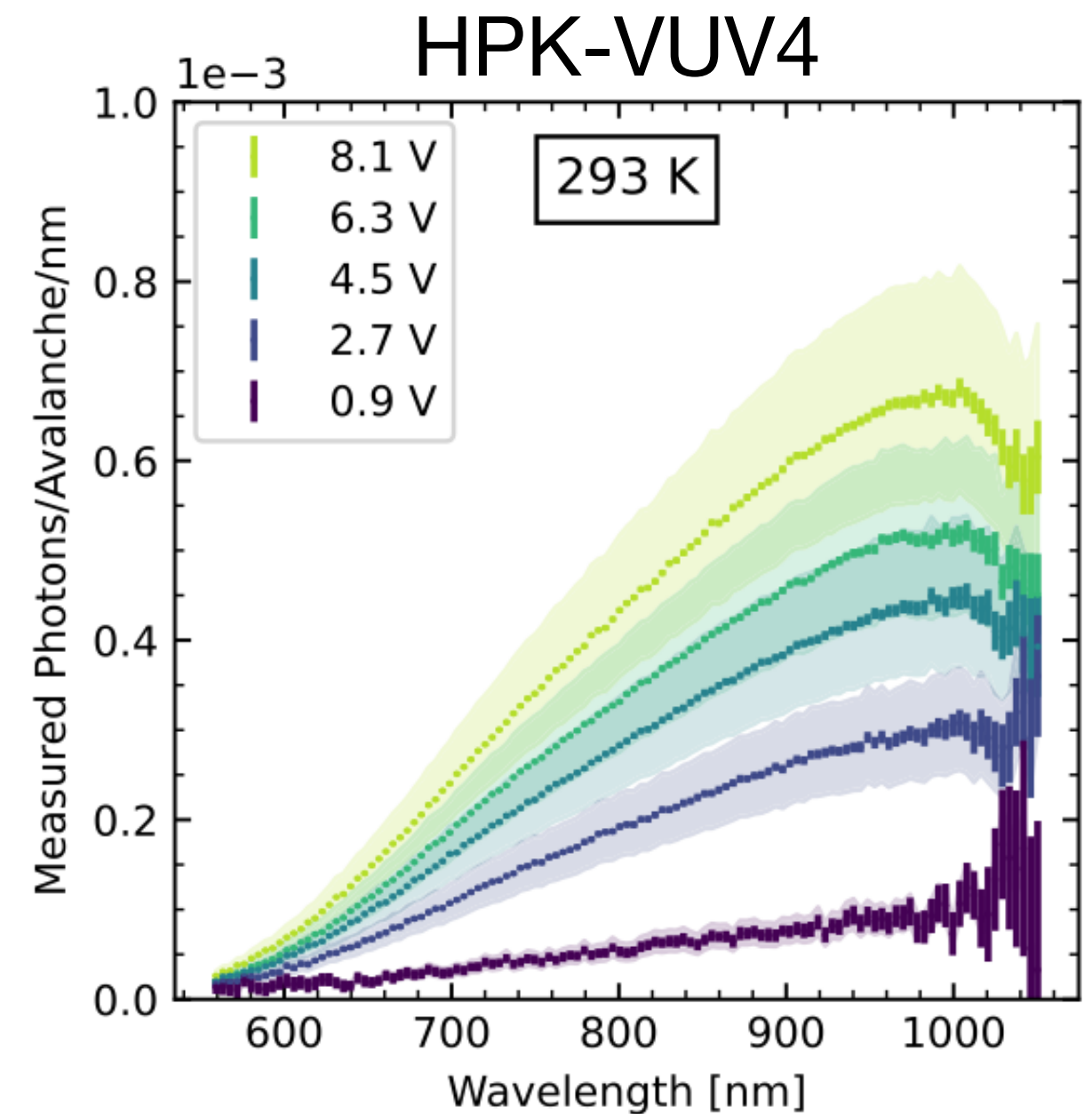
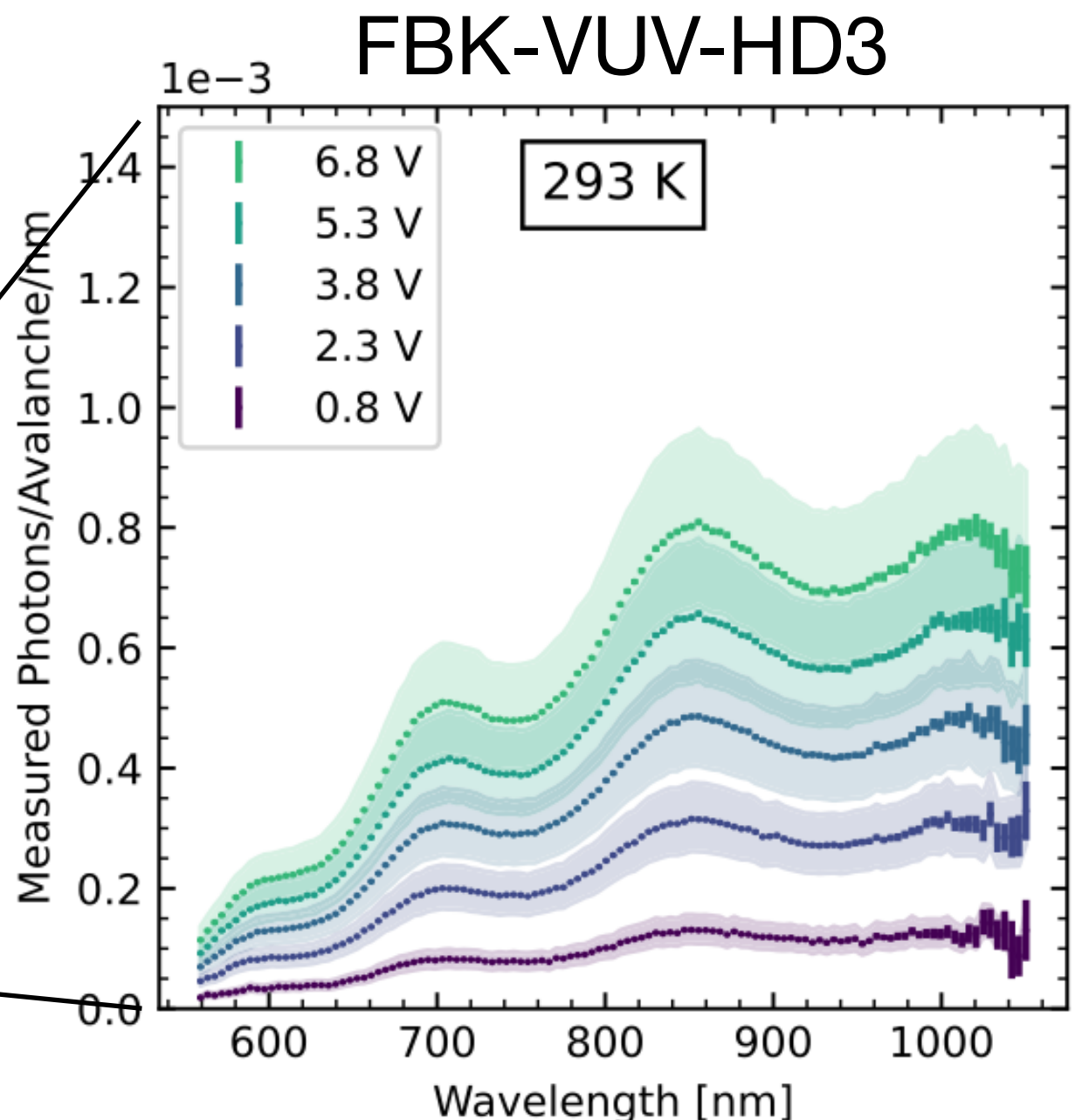
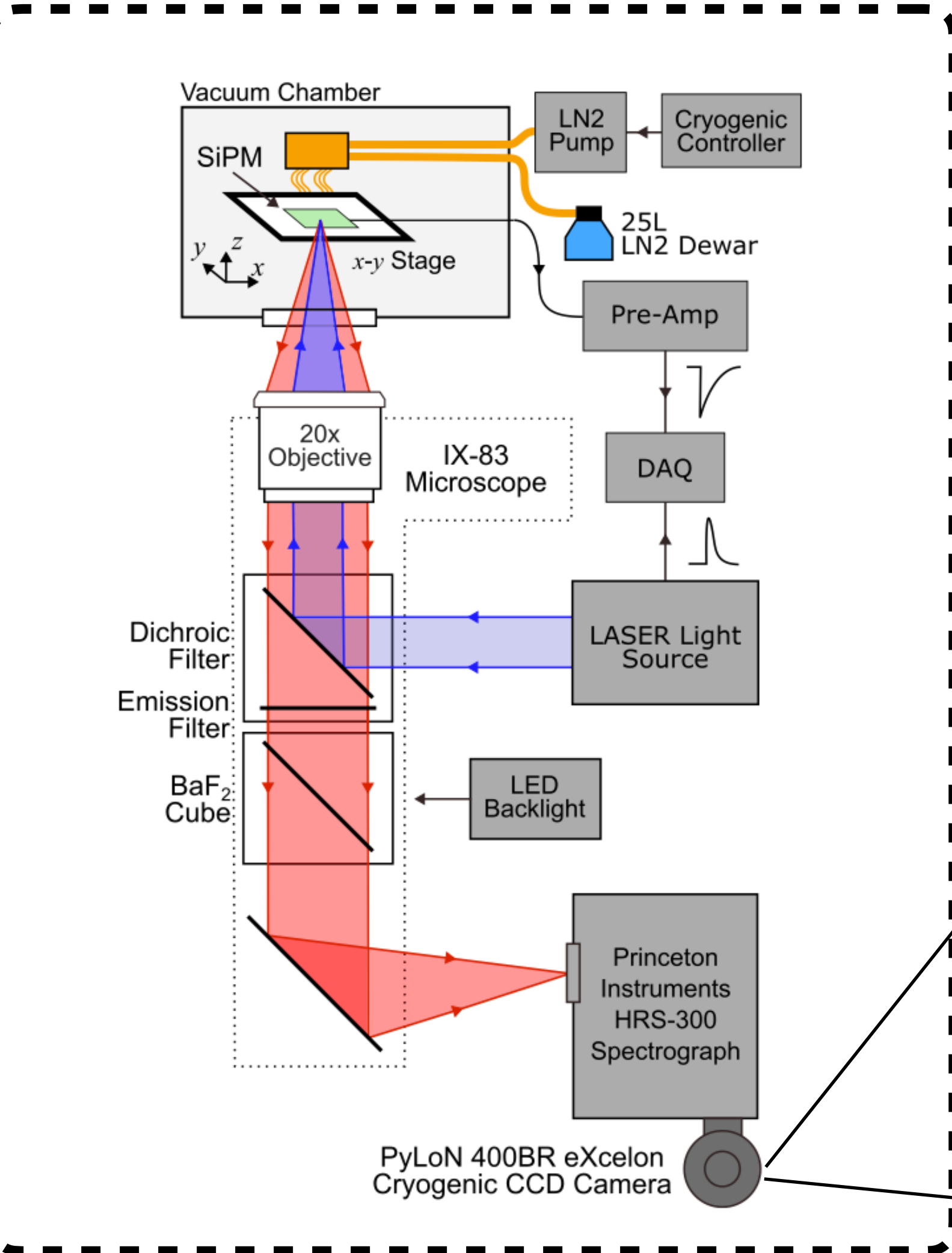
Tunable Wavelength Femtosecond Laser (I-OPA-TW)

- 310nm to 2800nm
- ~O(10nm) spectral width
- ~200 fs pulse duration

Stimulated Secondary Emission of SPADs

MIEL Detailed Outline

- During an Avalanche further photons are produced contributing to external cross talk.
- Large-area next generation physics experiments rely on SiPMs.
- MIEL was used to measure the spectra of secondary photons emitted from
 - Hamamatsu VUV4
 - Fondazione Bruno Kessler (FBK) VUV-HD3



Timing Measurements on Sherbrooke Digital SPAD

- **In Collaboration with Sherbrooke we were able to use MIEL to test one of their single Digital SPAD designs**
 - Individual SPAD with integrated CMOS readout.
 - Known structure information allows us to compare our data to model predictions of the device.
- **Timing Response modelling**
 - Can utilise simple diffusion models to probe the effect of doping on hole/electron transport in SPAD designs
 - Can leverage PDC ~ 10 ps resolution allowing us to see transport variations depending on device structure.
- **Feasibility of Two photon absorption in SPADs**
 - Can SPADs be used for Calorimetry?

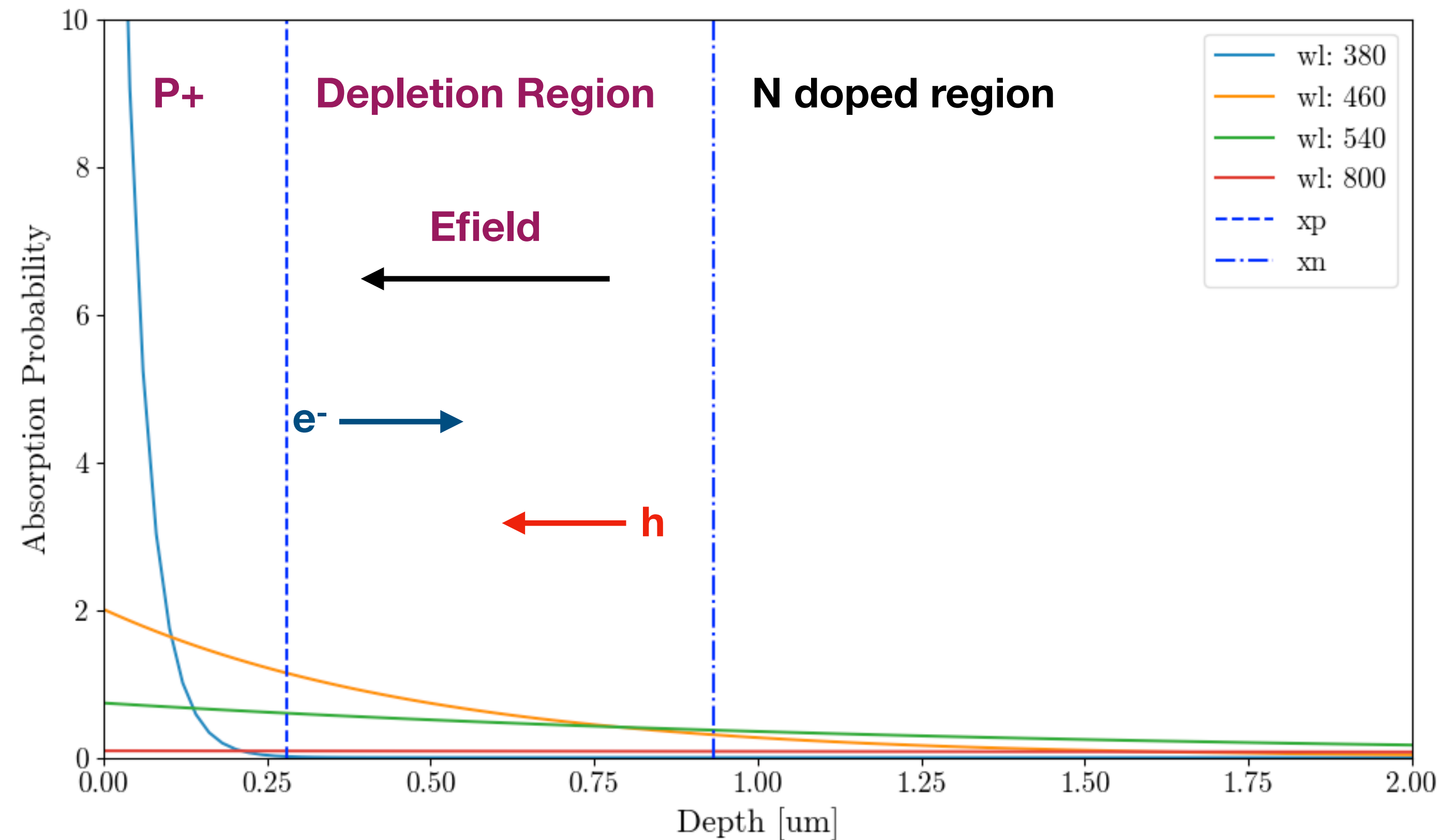


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Probing Charge Transport with Broad Spectrum

By using different wavelengths we can deposit charge at varying depths.

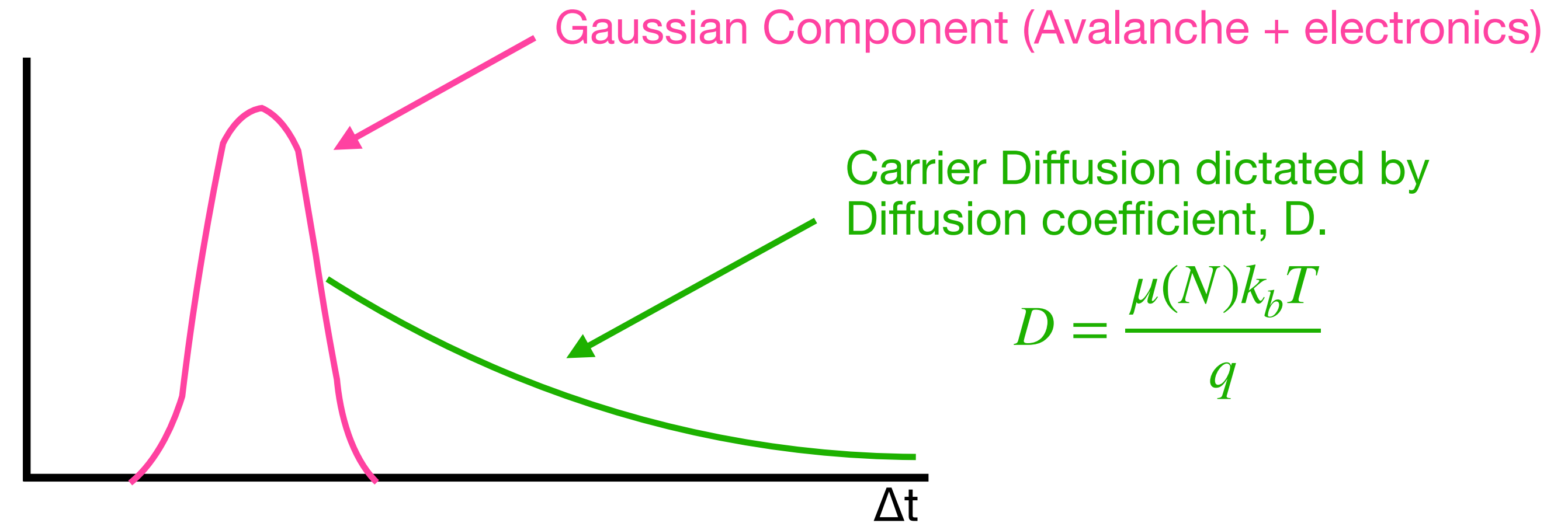
- @ $< 400\text{nm}$ we can deposit everything above the depletion region.
- @ $> 500\text{nm}$ we can start probing carrier diffusion from the bulk
- Used MIEL to probe how this affects the timing response of the device



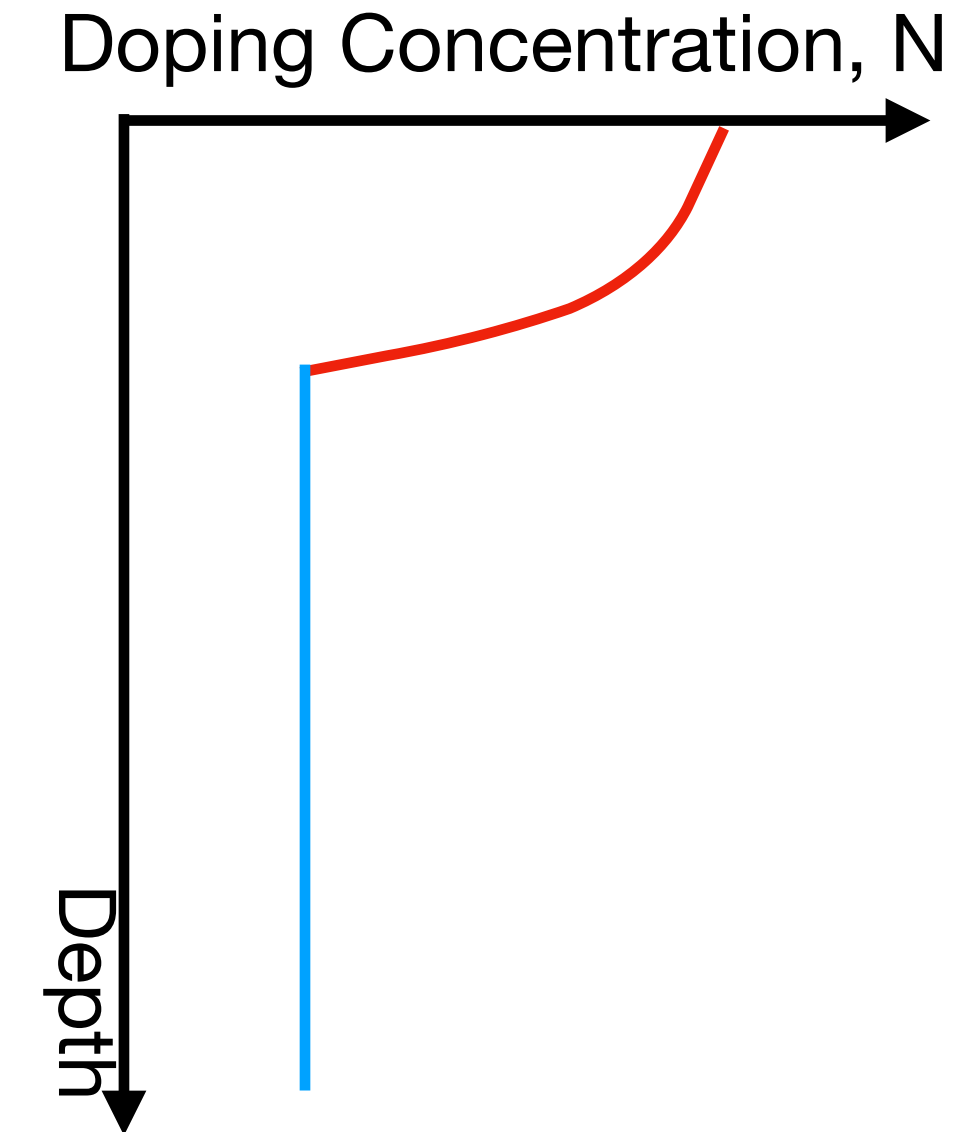
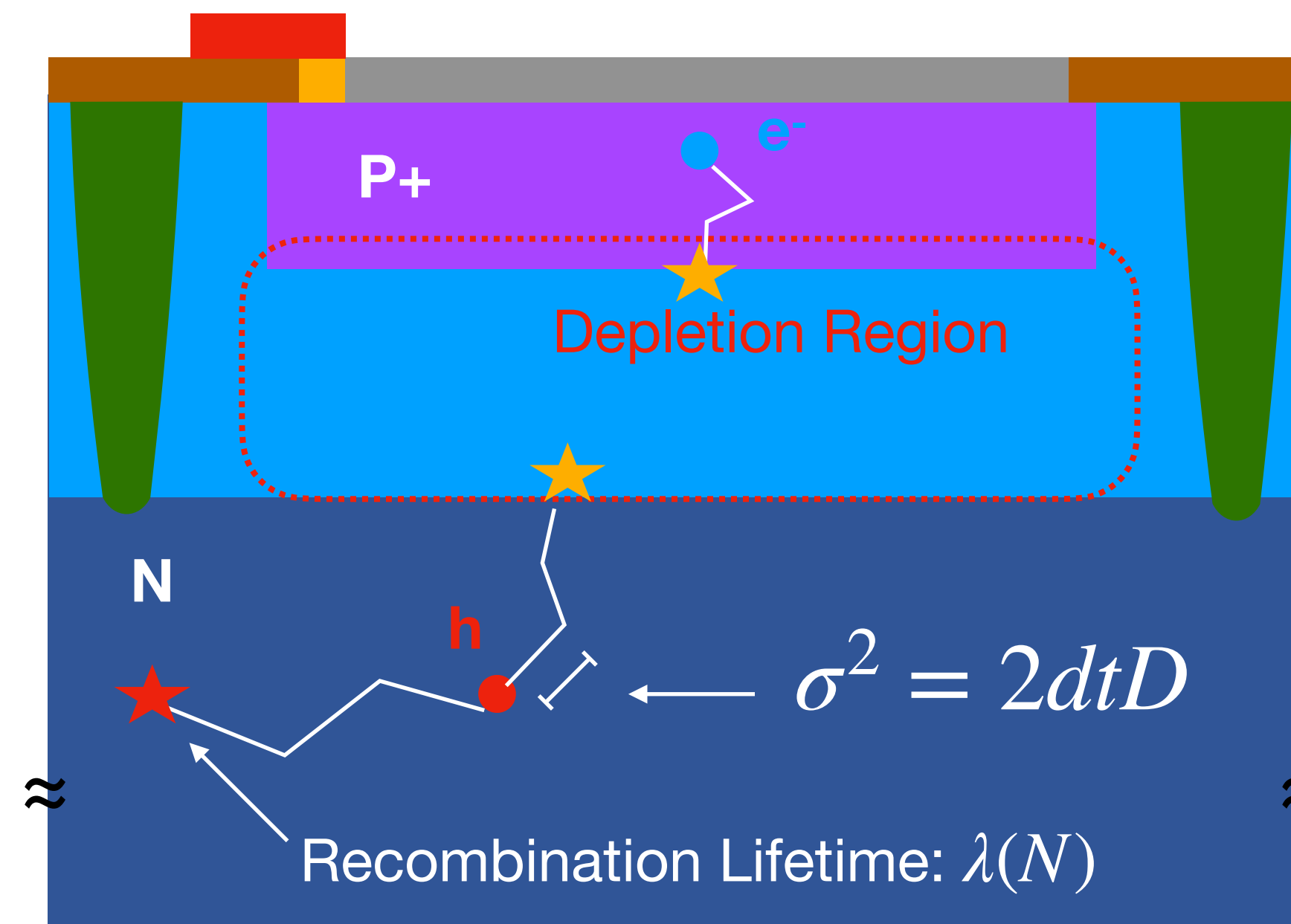
Simple Diffusion Time Response Model

Two Main Contributions

- ~Gaussian Avalanche Component
 - Dependent on Electric Field
 - Carrier Type e/h
 - Readout electronics
 - Fitted to empirical data
- Carrier Diffusion
 - Dependant on Mobility and Lifetime
 - Carrier type e/h
 - Treated as a Random walk.
- **Can separate contributions of electrons from P+ region and holes from N region**
 - Broadening of Gaussian component associated with electron diffusion from P+ region.
 - Mobility far lower in highly doped substrate.

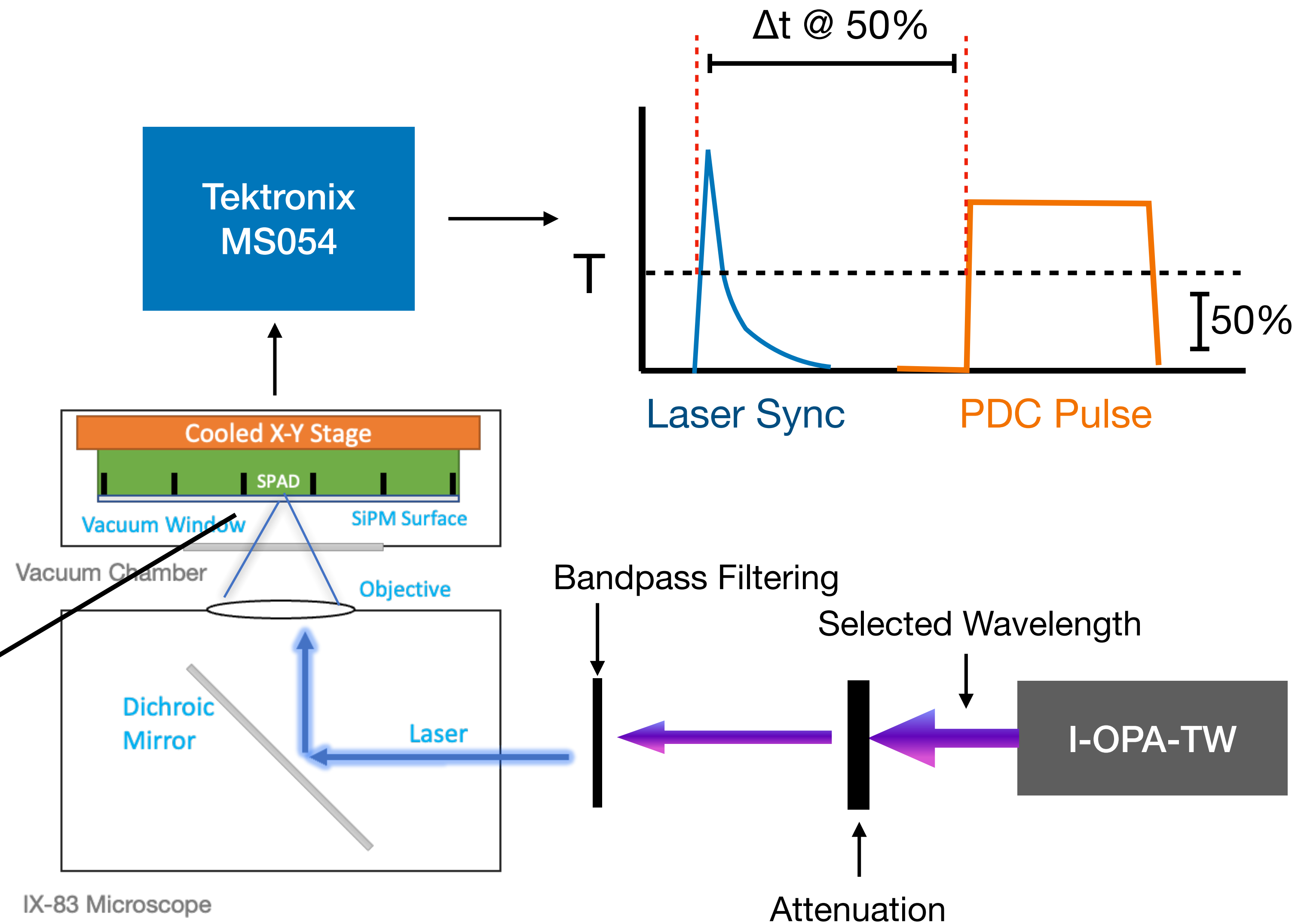
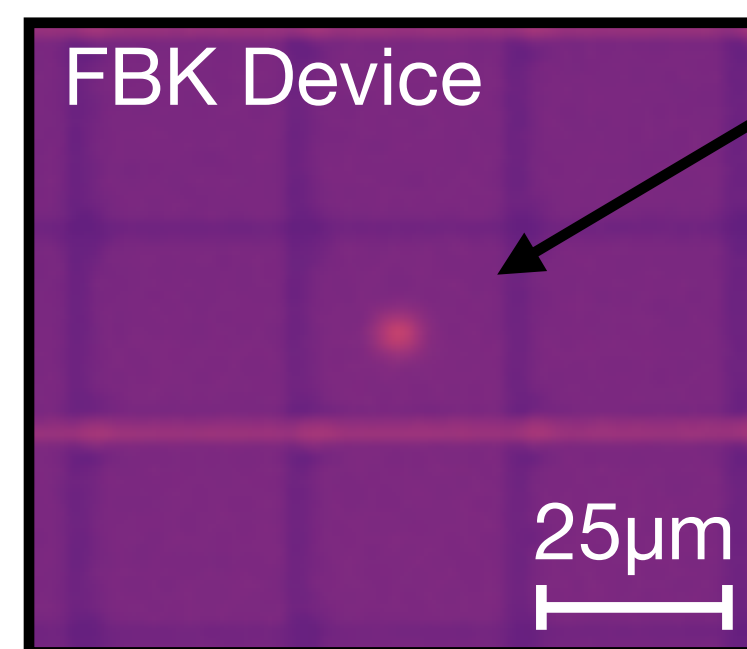


$$D = \frac{\mu(N)k_bT}{q}$$



Timing Response Measurement

- Selected a range of wavelengths between (380nm - 800nm)
 - Beam is attenuated and filtered
 - Time response calculated as difference between the laser sync rising edge and PDC output rising edge.
- Data Taken with Tektronix MS054 Scope
 - Trigger set at 50% of Waveform
- The time response of each wavelength was then compared to monte carlo simulation



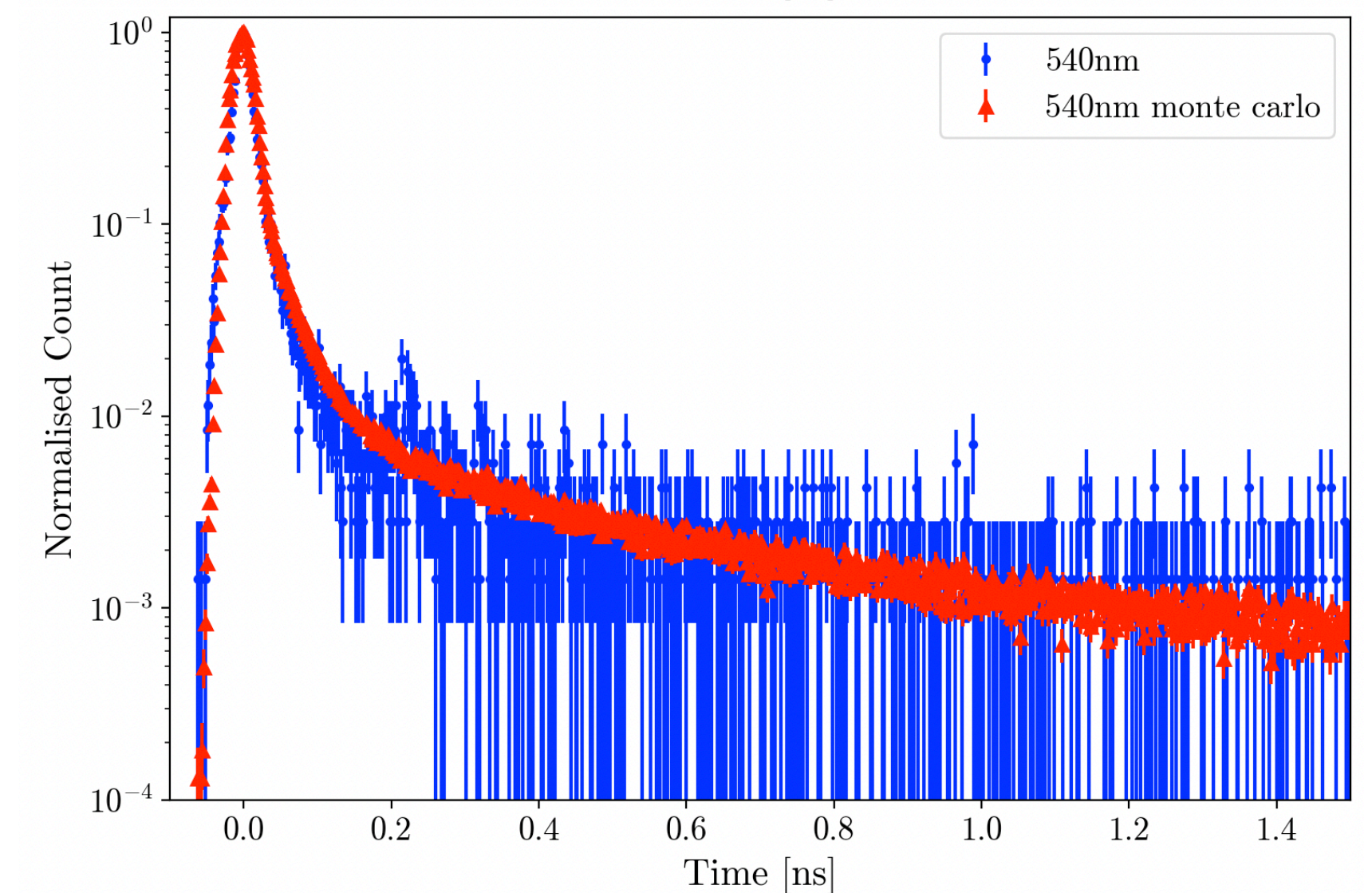
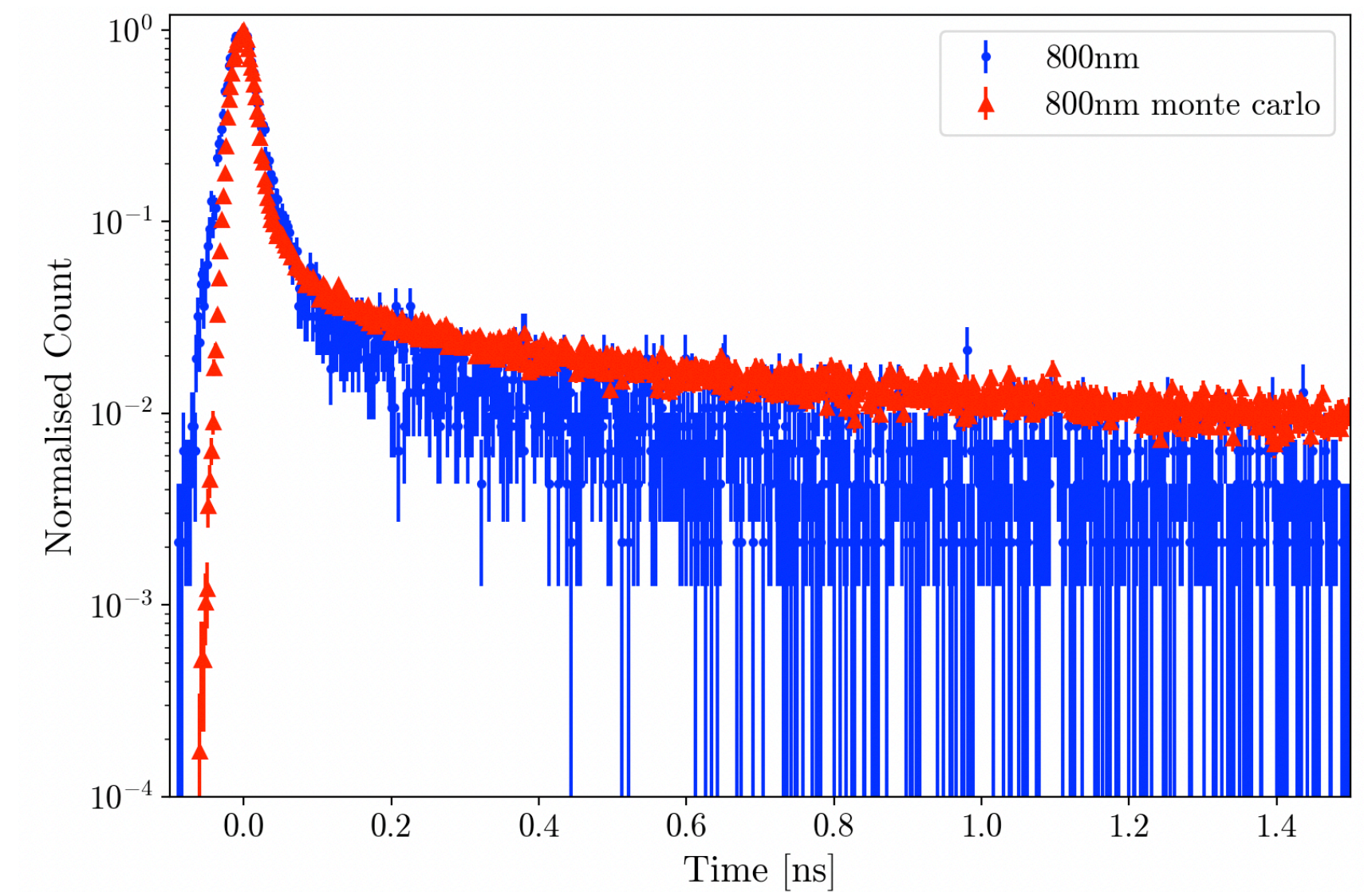
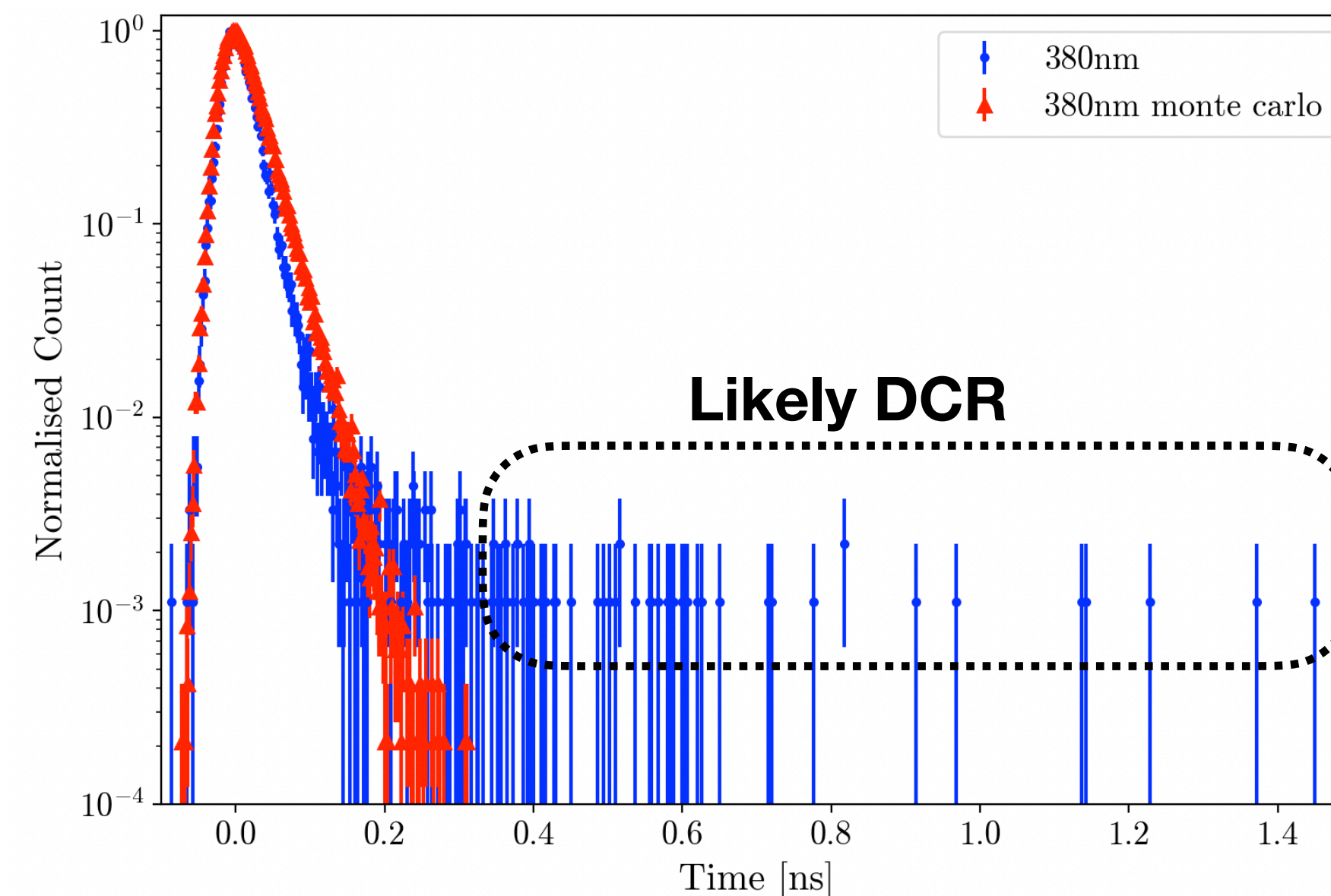
Investigating Hole Diffusion in PDC

Generally good agreement between Data and simple model.

- Tail dominated by hole diffusion
- Model starts to vary at higher wavelengths
- At 380nm almost nothing is deposited in the bulk below the depletion region.



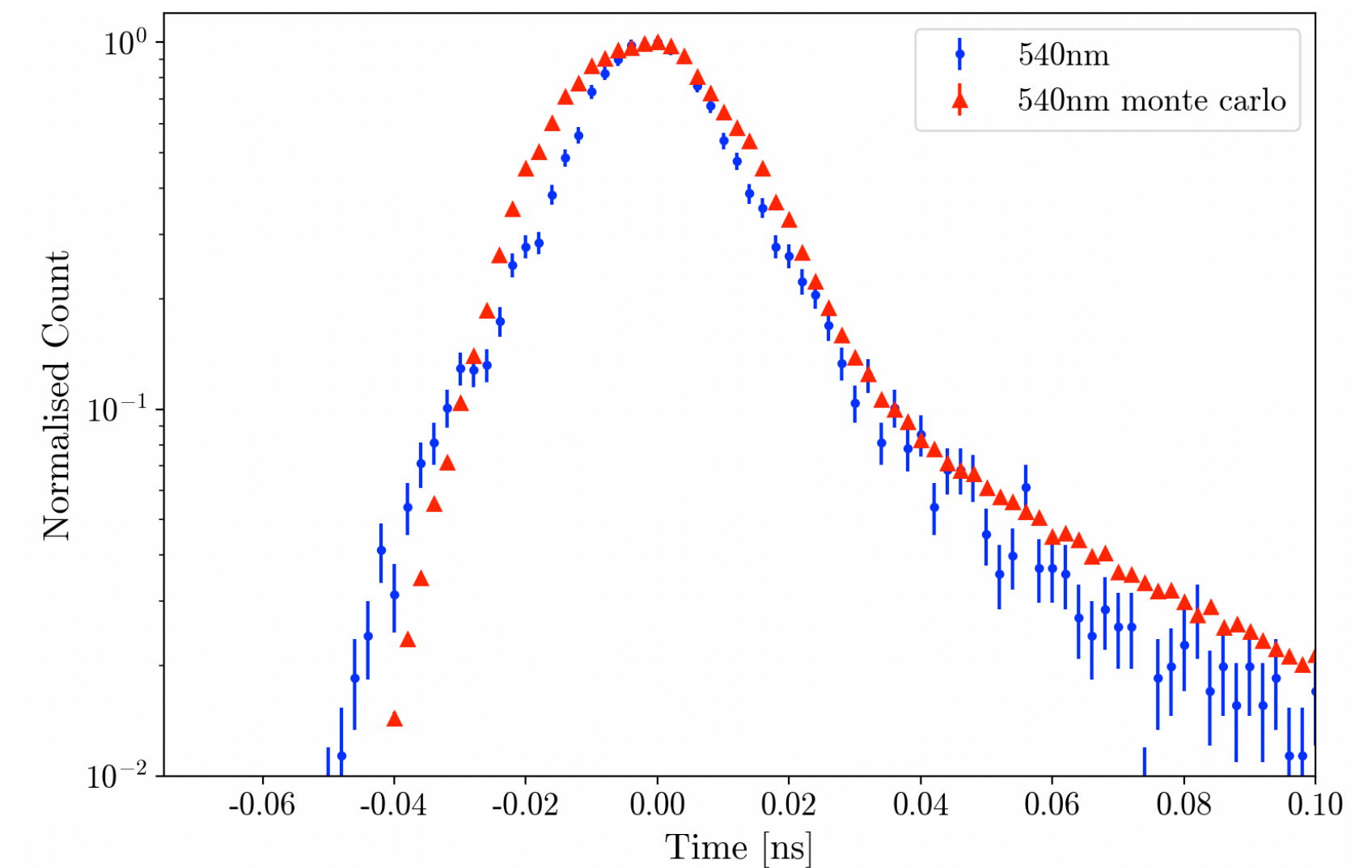
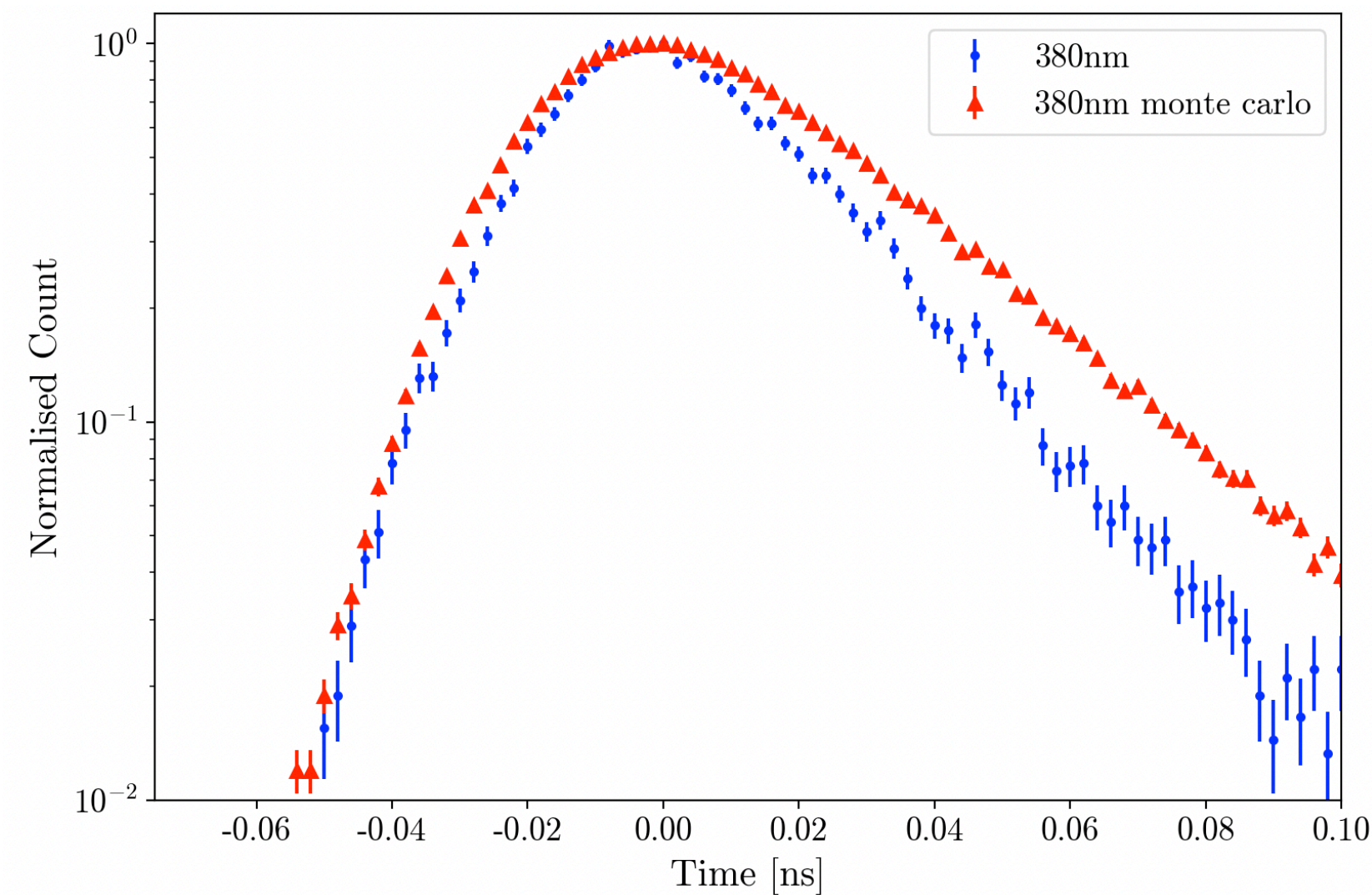
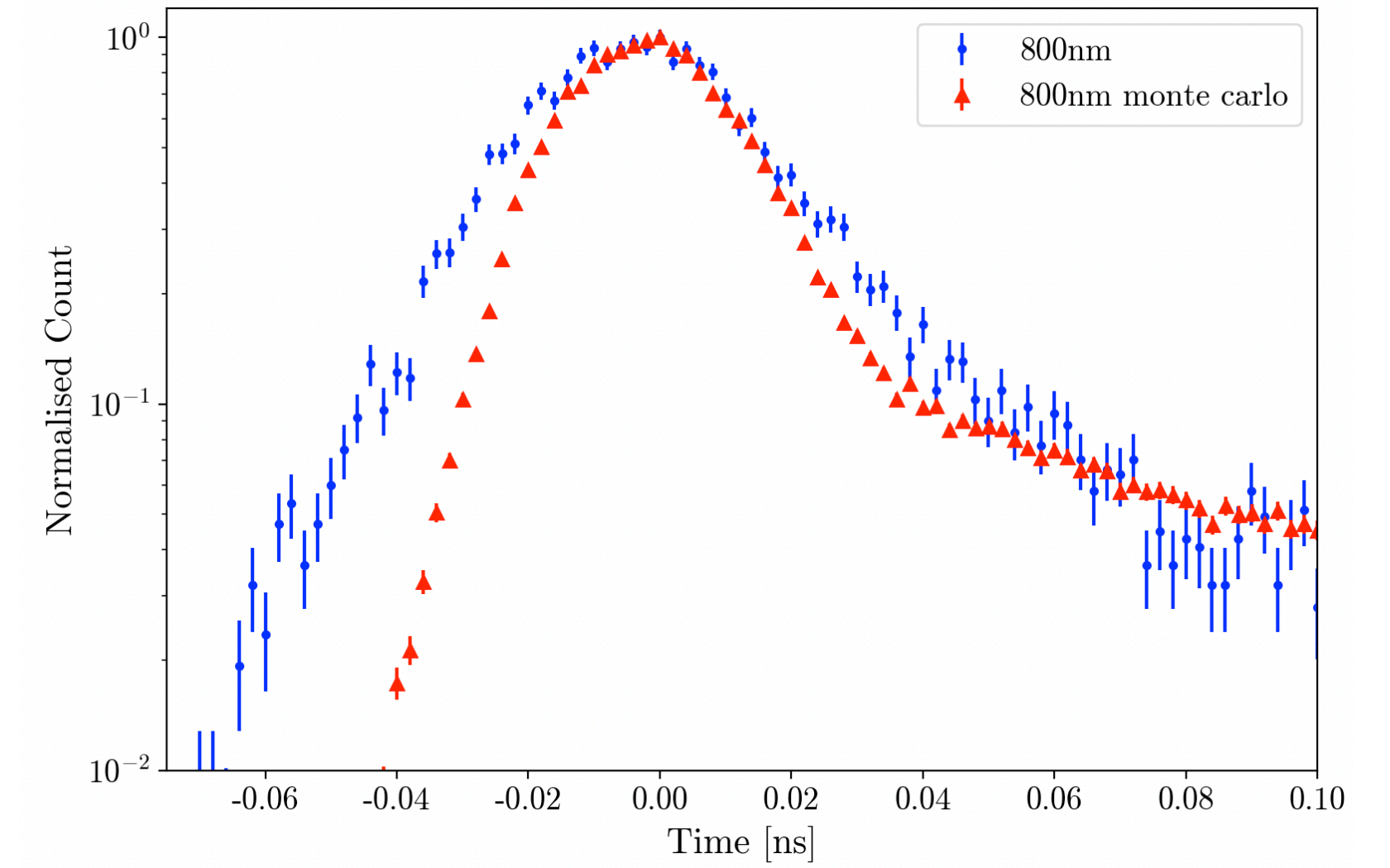
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Investigating Prompt Response of PDC

Generally good agreement between Data and simple model.

- At 380nm all carriers are deposited in the P region.
 - Model predicts a much broader gaussian at 380 due to worse electron mobility in highly P doped region.
- 540nm is generally good agreement
- 800nm: Substantial disagreement in the leading edge
 - Planning to retake this data.



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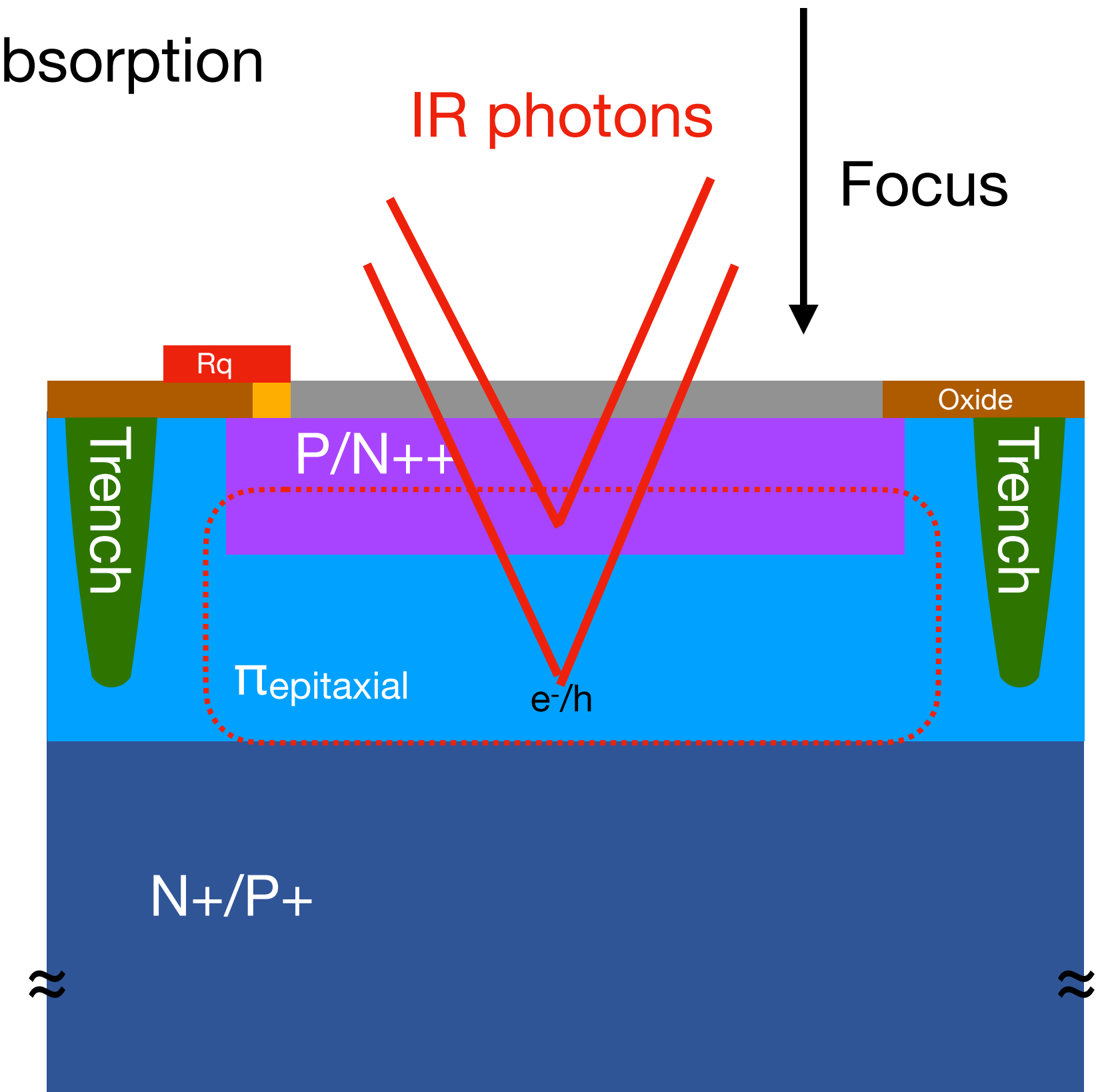
Two-Photon Absorption with SPADs

- Two Photon absorption (TPA) is the process by which the simultaneous absorption of two light quanta matches the materials bandgap energy (E_{bandgap}).
- The loss of Irradiance, I , with depth is modelled by :

$$\frac{dI}{dz} = \beta I^2$$

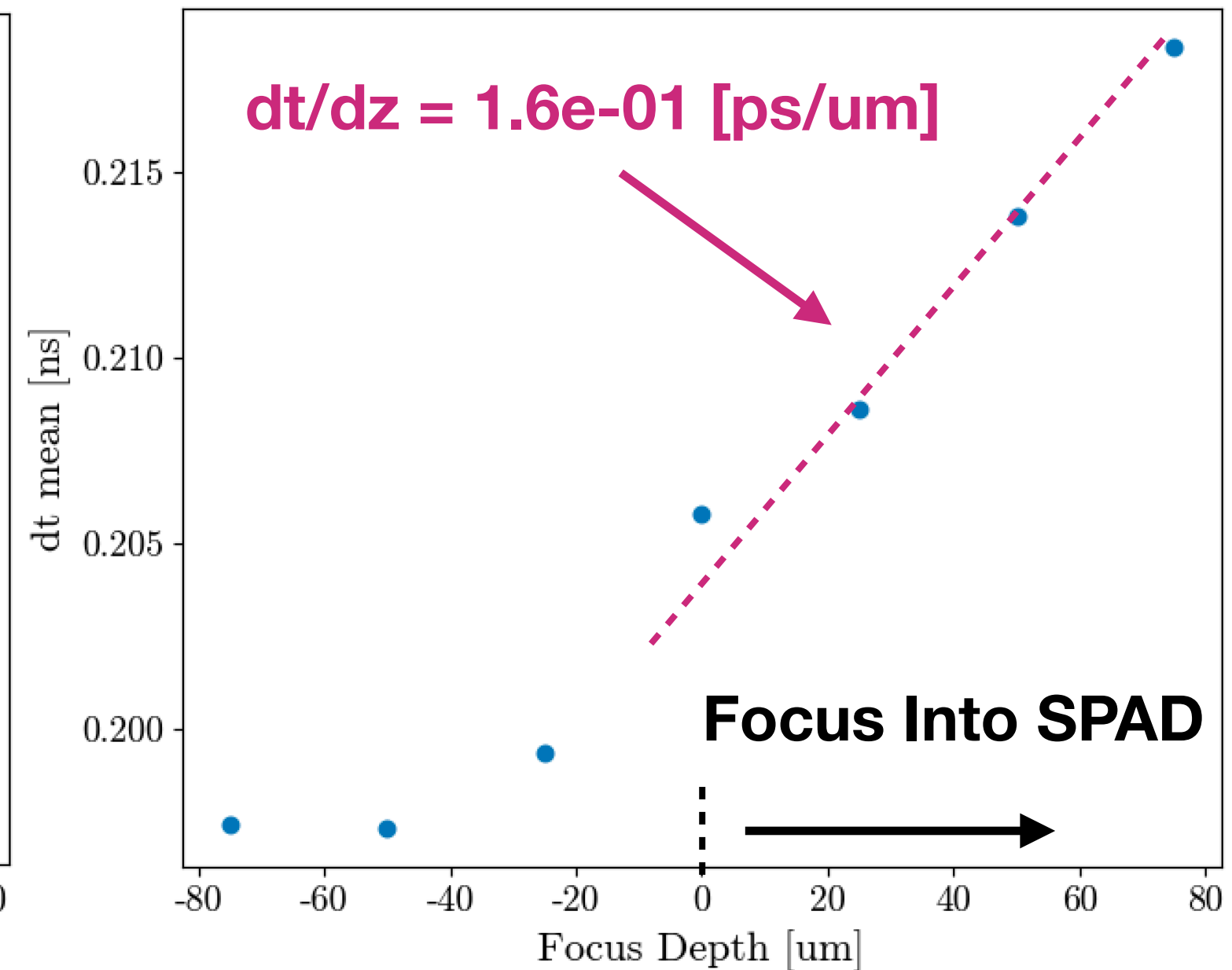
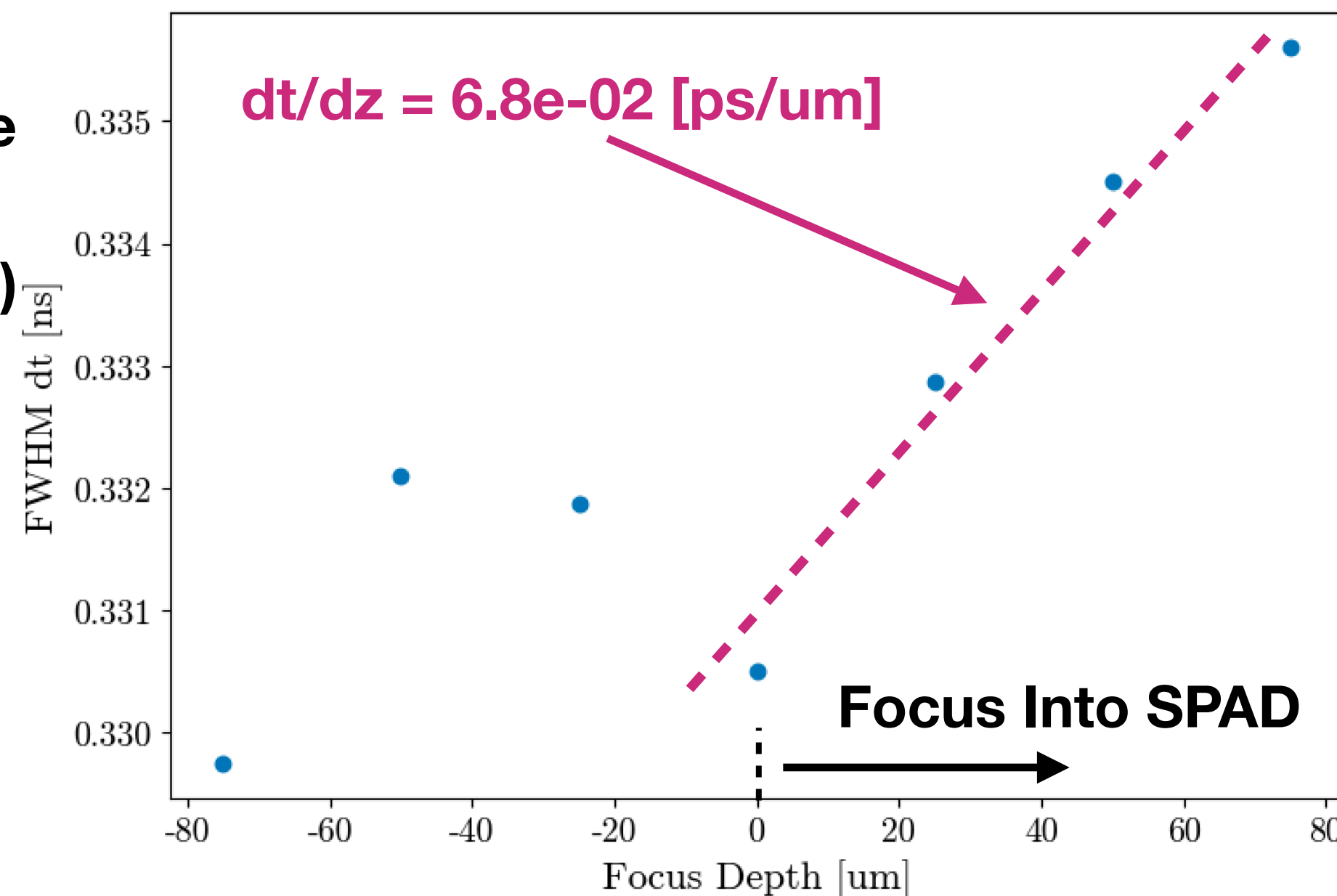
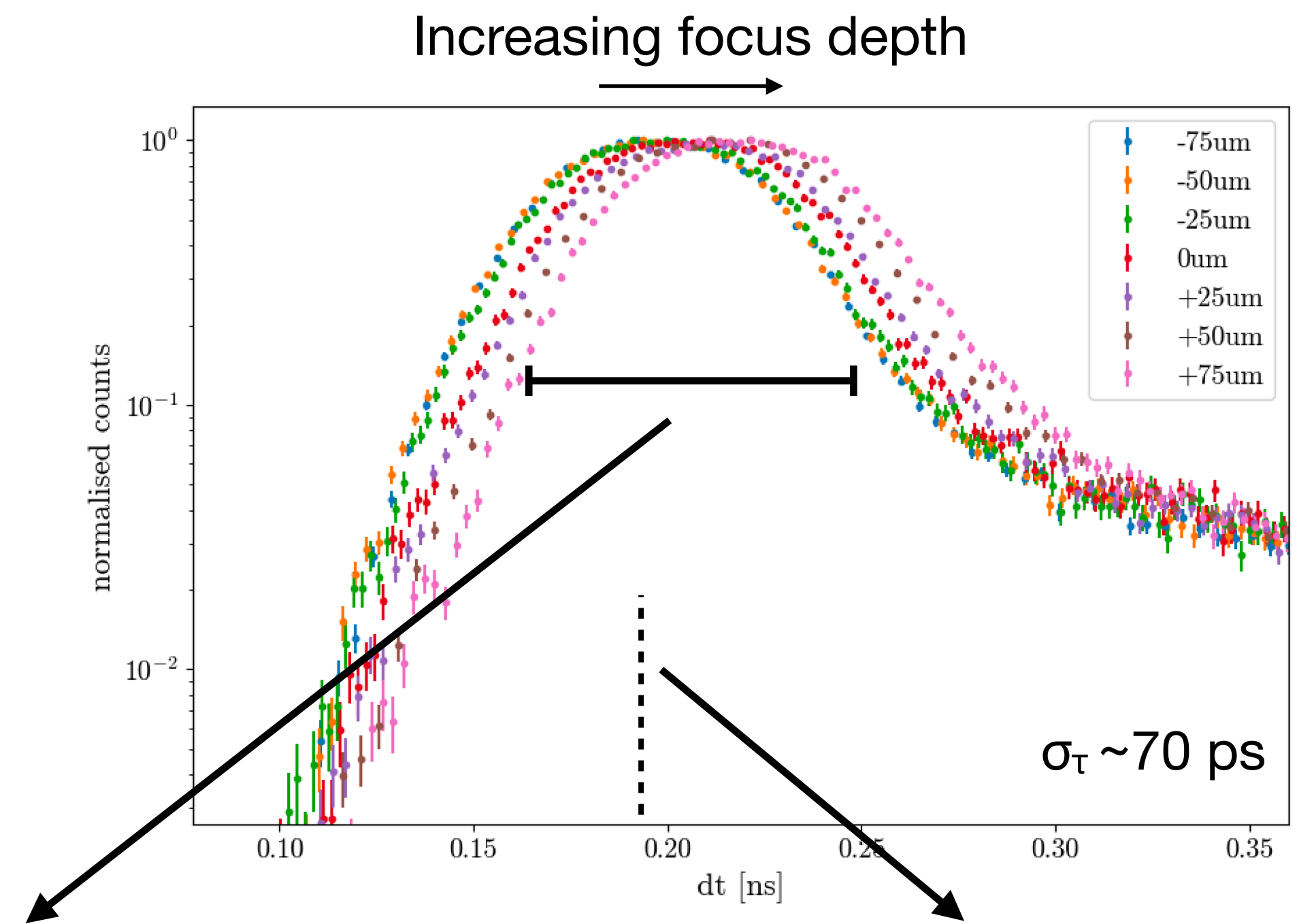
← TPA Coefficient

- Proven for silicon particle detectors (doi: 10.1109/TNS.2020.3044489)
- Fine control of charge deposition in SPAD devices.
- Could SPADs measure calorimetry information?



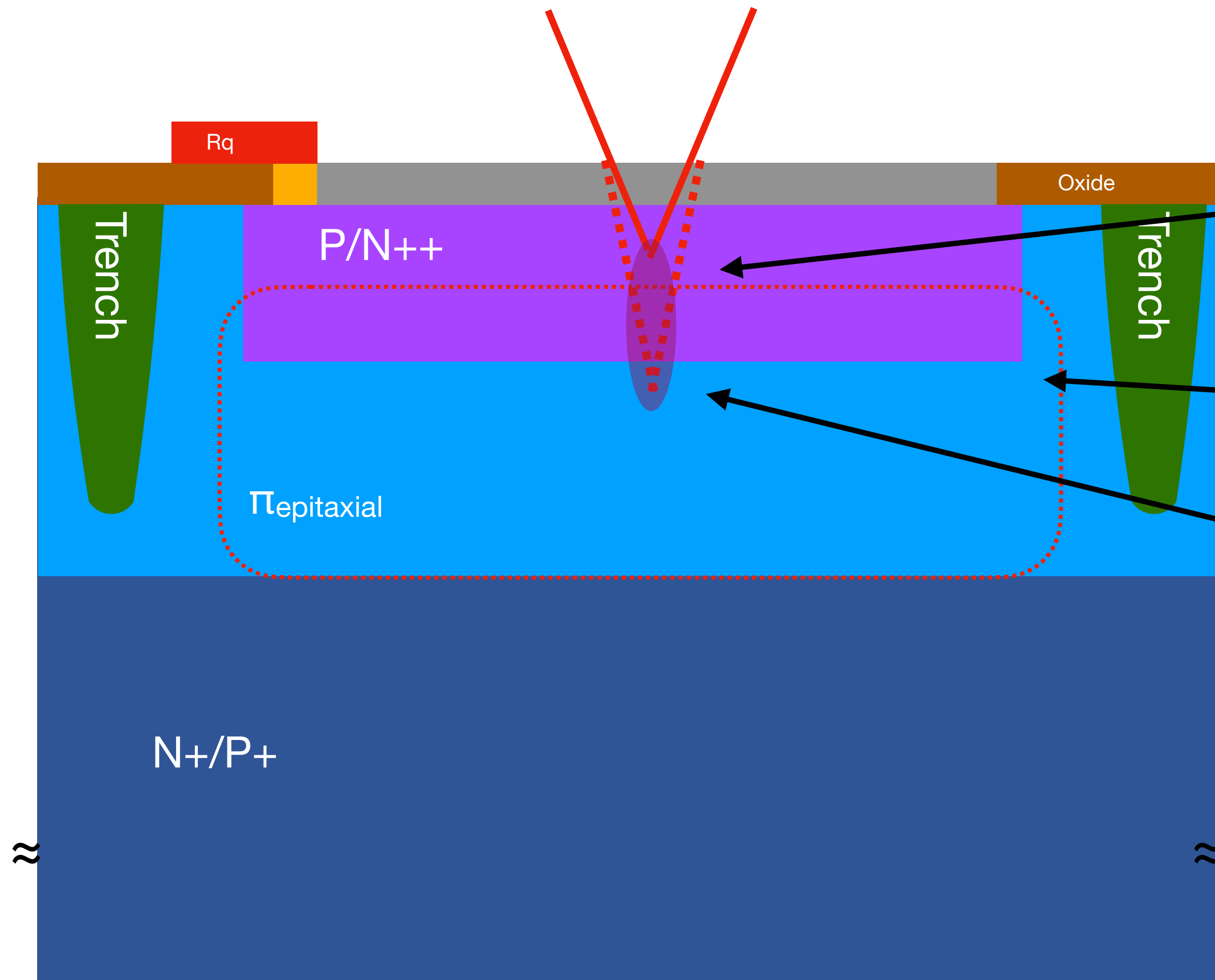
Initial Attempts at TPA

- Initial attempts used 1550nm laser ~200fs pulses focused with a 0.48 NA Olympus IR objective.
 - Took timing resolution data
 - Expected to see some affect to timing due to deposition depth
- Initial results are inconclusive (data was taken 2 weeks ago)
 - We see a linear shift in the prompt peak mean as we focus into the device.
 - We also see a shift in FWHM likely due to longer diffusion time from bulk
- Diffcult to discriminate whether we are seeing 1PA or 2PA.
- Still in the early stages (work on going)



See a linear trend with focus

Difficulties with TPA in SPAD's



Optical Limitations

- Due to index of refraction focus point is altered substantially
 - Can be combatted with higher NA objectives
- Kerr effect could play a role, change of refractive index due to applied electric field.
- SPAD Junction $\sim 0(\mu\text{m})$. Optical effects such as Rayleigh length make it difficult to focus beam to $< \mu\text{m}$ resolution
- Likely still dominated by single photon events.
- **Work in progress.**

Conclusions

- **At TRIUMF we have developed a test setup that allows us to broadly characterise SPAD Devices**
 - Femtosecond pulsed broad spectrum laser allows us to probe charge transport in these devices
 - Understanding effects at the picosecond level will aid in the design and development of future devices
 - Will aid in the development of new applications and the refinement of current ones.
- **Attempts at TPA in Digital SPAD shows some interesting effects in the timing distribution with varying focus.**
 - **Though still inconclusive there are some interesting things to keep us busy.**